

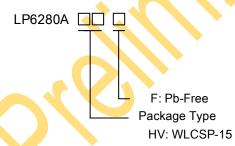


LP6280A Dual Output Power Supply for LCD Bias

Features

- Input voltage range: 2.7V to 5.5V
- Programmable output voltages
 - VOP output voltage: 4V to 6V with 0.1V per
 - VON output voltage: -6V to -4V with 0.1V per
- 150mA positive operation current and support 200mA load transient at VOP
- 150mA negative sink current at VON
- 85% efficiency at VIN=4.4V, VOP/VON = +/-5.4V, 150mA output per channel
- **I2C** Interface
 - Flexible Output Voltage Programming
 - Programmable Active Output Discharge
- **Protections**
 - Input under-voltage lockout (UVLO)
 - Boost cycle-by-cycle current-limit protection
 - Output current limit and short circuit protection
 - Thermal shutdown protection
- Packaging
 - WLCSP 15 balls (1.19mm x 1.96mm)
 - RoHS Compliant and Halogen Free
 - 100% Lead (Pb) Free

Order Information



General Description

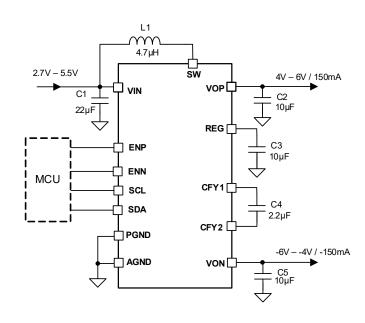
LP6280A The is designed to supply positive/negative driven applications. The device uses a single inductor scheme to provide both output currents. The integrated synchronous Boost converter provides a regulated voltage for a LDO and a charge pump. The LDO provides a regulated

and programmable positive bias VOP and the pump provides regulated programmable negative bias VON. The device offers low noise, small solution size and high efficiency. The other feature includes under-voltage (UVLO). lockout internal soft-start. cycle-by-cycle current limit and output over load and short circuit protection as well as thermal shutdown. The LP6280A is available in a space saving WLCSP 15-ball (0.4mm pitch) package.

Applications

- Small-, Medium-Size Bipolar LCD Displays
 - Smartphone, Tablet
 - Camera, GPS
 - Home Automation, Point-of-Sales
 - Wearables (Smart Watch, Activity Tracker)
- General Split-Rail Power Supply for
 - Differential Audio, Headphone Amplifier
 - Instrumentation, Operational Amplifier, Comparator
 - DAC/ADC

Typical Application Circuit





Device Information

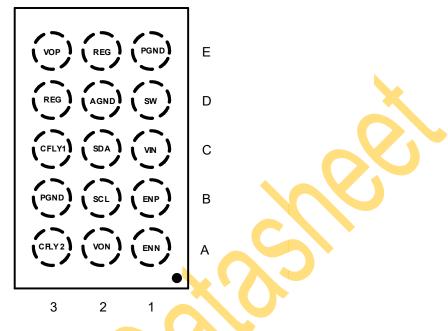
Part Number	Top Marking	Package	Moisture Sensitivity Level	Shipping				
LP6280A	LPS LP6280A YWX	WLCSP-15	MSL1	3K/REEL				
Marking indication: Y: Year Code, W: Week Code, X: Batch Numbers.								

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Pin Diagram



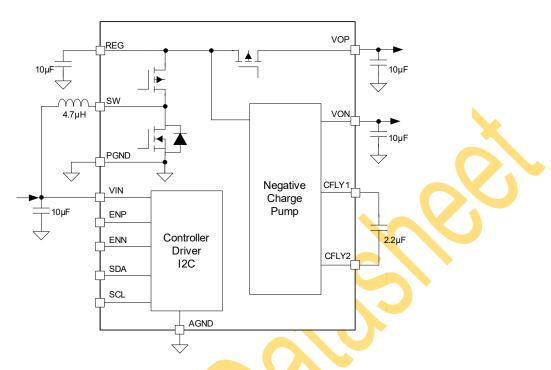
15-ball WLCSP (Top View)

Pin Description

I III De.	cripti	
Pin	Name	Description
A1	ENN	Enable input for VON rail.
A2	VON	Negative voltage output. Decouple this pin to PGND with a 10µF or higher ceramic
AZ	VON	capacitor as close to this pin as possible.
A3	CFLY2	Negative input for the external flying capacitor. Connect a terminal of a 2.2µF
AS	CFLYZ	ceramic capacitor close to this pin.
B1	ENP	Enable input for VOP rail.
B2	SCL	I <mark>2C int</mark> erface clock signal.
B3, E1	PGND	Power ground.
C1	VIN	Supply voltage input. Connect a 10µF ceramic capacitor from this pin to PGND.
C2	SDA	I2C interface data signal.
C3	CFLY1	Positive input for the external flying capacitor. Connect a terminal of a 2.2µF
C3	CFLYI	ceramic capacitor close to this pin.
D4	SW	Switching node output. Connect a terminal of an external inductor to this switching
D1	300	node. Short and wide trace is required for SW connection.
D2	AGND	Analog ground. Control circuitry returns current to this pin.
D3, E2	REG	Boost converter regulated output. Decouple this pin to PGND with a 10µF or higher
D3, ⊑2	KEG	ceramic capacitor as close to this pin as possible.
E3	VOP	Positive voltage output. Decouple this pin to PGND with a 10µF or higher ceramic
ES	VOP	capacitor as close to this pin as possible.



Functional Block Diagram



Absolute Maximum Ratings (1)

•	VIN, SW, REG, VOP, VCFLY1, SDA, SCL Volta	ge to GND0.3V to 7V
•	VENN, VENP Voltage to GND	
•	VON, VCFLY2 Voltage to GND	
•	Maximum Junction Temperature (TJ)	
•	Storage Temperature Range	40°C to 150°C
•	Maximum Soldering Temperature (at leads, 10 s	ec)260°C

Note: (1) Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD Susceptibility

• HBM(Human Body Model) ----- 2KV

• MM(Machine Model) ------ 200V





Recommended Operating Conditions

PARAMETER		MIN	NOM	MAX	UNIT
V _{IN}	Input Voltage	2.7		5.5	V
I _{VOP}	Positive Output Current	0		150	mA
I _{VON}	Negative Output Current	0		150	mA
V _{VOP}	Positive Output Voltage	4.0	5.5	6.0	V
V _{VON}	Negative Output Voltage	-6.0	-5.5	-4.0	V
TJ	Operating Junction Temperature Range (T _J)	-40		125	°C
TA	Ambient Temperature Range	-40		85	°C
θЈΑ	Thermal Resistance		85		°C/W
$\theta_{ extsf{JC}}$	Thermal Resistance		1		°C/W
L	Boost Inductance ⁽²⁾	3.76	4.7	5.64	μH
C _{IN}	Input Capacitance (2) (3)	4	10	30	μF
C _{REG}	Boost Output Capacitance(2) (3)	4	10	30	μF
C _{FLY}	Flying capacitance ^{(2) (3)}	0.9	2.2	2.64	μF
C _{VOP} , C _{VON} ,	Output Capacitance ^{(2) (3)}	4	10	30	μF

Note:

- (1) The transient output current is allowed up to 150mA with higher output voltage drop.
- (2) The values recommended in the table are effective inductance and capacitance.
- (3) X7R, 0603 size and 10V (or 16V) voltage rating capacitors are recommended





Electrical Characteristics

(The specifications are at T_A =25°C, V_{IN} = 3.7V, V_{OP} = 5V, V_{ON} = -5V, unless otherwise noted.)

Symbol Parameter		Condition	Min	Тур	Max	Units
INPUT VOL	TAGE AND CURRENT		1	•	1	1
V _{IN}	Input Voltage Range		2.7		5.5	V
lα	Input Supply Current	VENN and VENP are tied to AGND			1	μА
IQ	Input Supply Current			1		mA
V_{IN_UVLO}	Under Voltage Lockout of V _{IN}	V _{IN} Rising	2.2	2.4	2.65	٧
VIN_UVLO_HYS	V _{UVLO} Hysteresis	V _{IN} Falling		300		mV
SWITCHING	G BOOST CONVERTER					•
F_SW	Switching Frequency	The old DS is OSC frequency	0.96	1.2	1.44	MHz
I _{LIM}	Switch Current Limit			1.5		Α
D _{MAX}	Maximum Duty Cycle			90		%
R _{DSON_HS}	High-side MOSFET On-resistance			0.3		Ω
R _{DSON_LS}	Low-side MOSFET On-resistance			0.3		Ω
POSITIVE O	UTPUT VOLTAGE LDO					
V _{OP}	Positive Output Voltage Range	21 steps, each step 100mV	4.0		6.0	V
V_{OP_ACC}	Positive Output Voltage Accuracy		-1.0		+1.0	%
I _{OP}	Positive Output Current Range		0		150	mA
V_{DROP}	Dropout voltage	V _{OP} =5V, I _{OP} =150mA		350		mV
250	Line Regulation	V _{IN} =2.5V~4.2V, I _{OP} =150mA		1		%
\bigcirc ,	Load Regulation	I_{OP} =10mA to 150mA, V_{OP} =5.4V		1		%
R _{DIS_P}	VOP Discharge Resistance	V _{OP} = 5.4V		40		Ω
V _{ENP(H)}			1.2			V
$V_{ENP(L)}$					0.4	V
I _{ENP}	ENP Sink Current	V _{ENP} =2V		10		μA
I _{LIM}	Output Current Limit			0.30		Α
I _{SCP}	Short Circuit Protection	V _{OP} < 40% of regulation		0.15		Α





Electrical Characteristics (Continued)

(The specifications are at T_A =25°C, V_{IN} = 3.7V, V_{OP} = 5V, V_{ON} = -5V, unless otherwise noted.)

NEGATIVE (NEGATIVE OUTPUT VOLTAGE CHARGE PUMP										
F _{CP}	Negative Charge Pump Switching Frequency		0.96	1.2	1.44	MHz					
V _{ON}	Negative Output Voltage Range	21 steps, each step 100mV	-6.0		-4.0	V					
V _{ON_ACC}	Output Voltage Accuracy		-1.5		+1.5	%					
I _{ON}	Negative Output Current Range		-150		0	mA					
V_{DROP}	Dropout voltage	V _{OP} =5V, I _{OP} =150mA		350		mV					
	Line Regulation	V _{IN} =2.5V~4.2V, I _{OP} =-150mA		1		%					
	Load Regulation	I _{ON} =-150mA to -10mA, V _{ON} =-5.4V	40	1.5		%					
R _{DIS_N}	VON Discharge Resistance	V _{ON} =5.4V		30		Ω					
V _{ENN(H)}			1.2			V					
V _{ENN(L)}			U		0.4	V					
I _{ENN}	ENN Sink Current	V _{ENN} =2V		10		μA					
I _{SHORT}	Output Short Current			0.15		Α					
THERMAL S	HUTDOWN PROTECTION										
T _{SHUT}	Thermal Shutdown	Temperature Rising		140		°C					
T _{SHUT_HYST}	Thermal Shutdown Hysteresis	Temperature Falling		30		°C					





Electrical Characteristics (Continued)

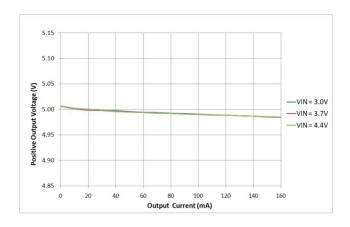
(The specifications are at T_A =25°C, V_{IN} = 3.7V, V_{OP} = 5V, V_{ON} = -5V, unless otherwise noted.)

Symbol	Parameter Condition		Min	Тур	Max	Units					
I2C Compatible Timing Specifications (SCL, SDA), referred to Figure 8											
r.	CCL alack fraguency	Standard Mode			100	kHz					
f _{SCL}	SCL clock frequency	Fast Mode			400	kHz					
1	Law raniad of the COL plant.	Standard Mode	4.7			us					
tLOW	Low period of the SCL clock	Fast Mode	1.3			us					
	Link maried of the CCL shade	Standard Mode	4.0			us					
tнісн	High period of the SCL clock	Fast Mode	0.6			us					
	Bus free time between a	Standard Mode	4.7			us					
t _{BUF}	STOP and START condition	Fast Mode	1.3			us					
1	Hold time for a repeated	Standard Mode	4.0			us					
thd, sda	START condition	Fast Mode	0.6	J		us					
1	Data actus tima	Standard Mode	0.25			us					
t _{SU, DAT}	Data setup time	Fast Mode	0.1			us					
4	Data hald time	Standard Mode	0.05		3.45	us					
thd, dat	Data hold time	Fast Mode	0.05		0.9	us					
_	Dies time of CDA signal	Standard Mode	20+0.1C _B		1000	ns					
t _{RDA}	Rise time of SDA signal	Fast Mode	20+0.1C _B		300	ns					
1	Fall time of CDA signal	Standard Mode	20+0.1C _B		300	ns					
t fda	Fall time of SDA signal	Fast Mode	20+0.1C _B		300	ns					
1	Setup time for STOP	Standard Mode	4.0		-						
t su,sto	condition	Fast Mode	0.6		-						
Св	Capacitive load for SCL and		_	_	0.2	nF					
06	SDA				0.2	- '''					



Typical Characteristics

VIN=3.7V, VOP=5V, VON=-5V, TA=+25°C, unless otherwise noted.



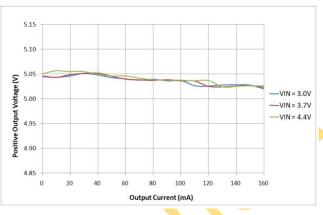


Figure 1. Positive Output Voltage VOP vs. Output Current

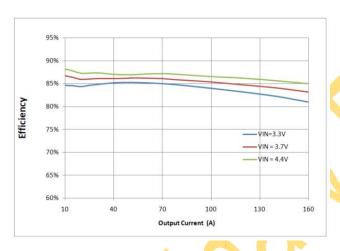


Figure 3. Efficiency ($V_{VOP} = 5V$, $V_{VON} = -5V$)

Figure 2. Negative Output Voltage Von vs. Output Current

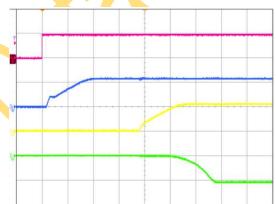


Figure 4. VOP and VON Enable CH1: ENP = ENN = 0 to 1, 5V/div, CH2: V_{REG} , 5V/div, CH2: V_{OP} , 5V/div, V_{ON} , 5V/div, Time: 500us/div)





Typical Characteristics (Continued)

VIN=3.7V, VOP=5V, VON=-5V, TA=+25°C, unless otherwise noted.

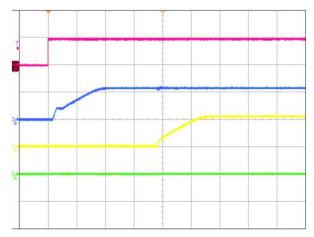


Figure 5. VON Enable

CH1: ENP = ENN = 0 to 1, 5V/div, CH2: V_{REG} , 5V/div, CH2: V_{OP} , 5V/div, V_{ON} , 5V/div, Time: 500us/div)

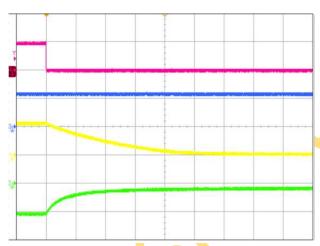


Figure 6. VOP and VON Disable

CH1: ENP = ENN = 1 to 0, 5V/div, CH2: V_{REG}, 5V/div, CH2: V_{OP}, 5V/div, V_{ON}, 5V/div, Time: 500us/div)

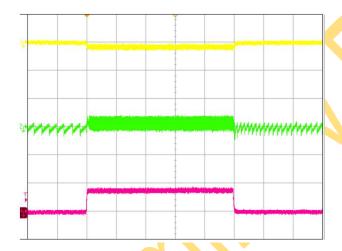


Figure 7. Load transient response'

(CH1: V_{OP} , 100 mV/div, CH2: VON, 100 mV/div, CH3: lout,

100mA/div, Time: 500us/div)



Detailed Description

Overview

The LP6280A supports input voltage range from 2.7 V to 5.5 V, operates with a single inductor scheme to provide a high efficiency with a small solution size. The synchronous boost converter generates a positive voltage that is regulated down by an integrated LDO, providing the positive supply rail (V_{OP}) . The negative supply rail (V_{ON}) is generated by an integrated negative charge pump (or CPN) driven from the boost converter output pin REG.

Undervoltage Lockout (UVLO)

The LP6280A integrates an undervoltage lockout block (UVLO) that enables the device once the voltage on the VIN pin exceeds the UVLO threshold. No output voltage will be generated as long as the enable signals are not pulled HIGH. The device, as well as all converters (Boost converter, LDO, CPN), will be disabled as soon as the VIN voltage falls below the UVLO threshold.

Power Enable

The LDO (VOP) and the negative charge pump (VON) are turned on/off by external enable signals. ENP pin is enable control input for VOP and ENN is enable control input for VON. If any enable signal is pulled high, Boost will be enabled once V_{IN} meets UVLO voltage level.

Boost Converter

The LP6280A integrates a PWM synchronous Boost converter operating with current mode control and 1.2MHz (typ) switching frequency. The device is designed for high efficiency over wide output current range.

VOP and VON Discharge

When VIN falls below UVLO threshold or both ENP and ENN pins are pulled low, all regulators will be turned off. If both ENP and ENN go low, VOP and VON will be actively discharged to GND.

Power Sequencing

The LP6280A Boost powers up if any of ENP and ENN is pulled high. If the Boost powers up successfully within 2ms, Boost Power Good signal is sent to enable VOP and/or VON rail(s). VOP startup time is about 1ms and VON startup time is about 1.5ms. VOP and VON rails can be enabled sequentially or simultaneously. Similarly, VOP and VON rails can be disabled sequentially or simultaneously. Boost powers off only when both ENP and ENN are pulled low.

Thermal Shutdown Protection

The LP6280A device enters over temperature protection if its junction temperature exceeds 140°C (typical). During over temperature protection the device is shut down. Once the junction temperature falls below the hysteresis threshold, the device restarts.



I2C Interface Specification

The LP6280A can easily modify parameters by I2C bus and the slave address is 0x3E. I2C is a two wire serial interface developed, the bus consists of a clock line (SCL) and a data line (SDA) with pull-up structures. The LP6280A works as a slave mode, and address is 0x3E. The data transfer protocol follow I2C-Bus Specification's standard mode (100kbps) and fast mode (400kbps).

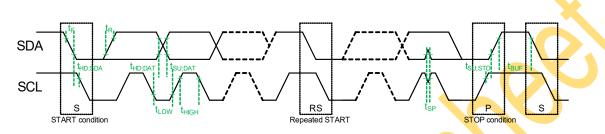


Figure 8. START and STOP Conditions

Write Data to Register

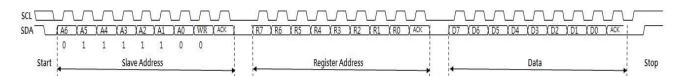


Figure 9. Write Single Byte Data to Register

Read Data to Register

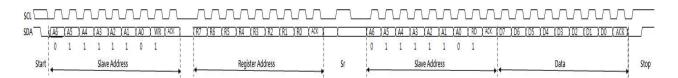


Figure 10. Read Single Byte Data from Register



Register Maps

Address	Description	Default	D7	D6	D5	D4	D3	D2	D1	D0
00H	SetVOP Voltage	0x0F		-	-	VOP [4:0]				
01H	SetVON Voltage	0x0F		-		VON [4:0]				
U3H	Set Discharge Resistor	0x03							DIS_	DIS_
03H	Enable	0x03			1				VOP	VON
FFH	Set Control Register	0x00	WR		ı		1			

Set VOP Voltage (Register Address – 00H)

VOP Voltage										
Addr: 00H	Addr: 00H Default Value: VON Register=0x0F, (VOP =5.5V)									
D7	D6	D5	D4	D3	D2	D1	D0			
R	R	R	R/W	R/W	R/W	R/W	R/W			
0	0	0	VOP[4]	VOP [3]	VOP [2]	VOP [1]	VOP [0]			

VOP [4:0]									
Register	Volt (V)	Register	Volt (V)						
00000	4.00	10000	5.60						
00001	4.10	10001	5.70						
00010	4.20	10010	5.80						
00011	4.30	10011	5.90						
00100	4.40	10100	6.00						
00101	4.50	10101	Reserved						
00110	4.60	10110	Reserved						
00111	4.70	10111	Reserved						
01000	4.80	11000	Reserved						
01001	4.90	11001	Reserved						
01010	5.00	11010	Reserved						
01011	5.10	11011	Reserved						
01100	5.20	11100	Reserved						
01101	5.30	11101	Reserved						
01110	5.40	11110	Reserved						
01111	5.50	11111	Reserved						

Set VON Voltage (Register Address – 01H)

VON Voltage										
Addr: 01H	dr: 01H Default Value : VON(Register)=0x0FH, VON =-5.5V									
D7	D6	D5	D4	D3	D2	D1	D0			
R	R	R	R/W	R/W	R/W	R/W	R/W			
0	0	0	VON[4]	VON [3]	VON [2]	VON [1]	VON [0]			

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VON[4:0]	VON[4:0]									
Register	Volt (V)	Register	Volt (V)							
00000	-4.00	10000	-5.60							
00001	-4.10	10001	-5.70							
00010	-4.20	10010	-5.80							
00011	-4.30	10011	-5.90							
00100	-4.40	10100	-6.00							
00101	-4.50	10101	Reserved							
00110	-4.60	10110	Reserved							
00111	-4.70	10111	Reserved							
01000	-4.80	11000	Reserved							
01001	-4.90	11001	Reserved							
01010	-5.00	11010	Reserved							
01011	-5.10	11011	Reserved							
01100	-5.20	11100	Reserved							
01101	-5.30	11101	Reserved							
01110	-5.40	11110	Reserved							
01111	-5.50	11111	Reserved							



Discharged Resistor Enable/Disable								
Addr: 03H Default Value : DIS_VO(Register)=0x03H								
D7	D6	D5	D4	D3	D2	D1	D0	
R	R	R	R	R	R	R/W	R/W	
0	0	0	0	0	0	DIS_VOP	DIS_VON	

DIS_VOP		DIS_VON			
Register	DIS_VOP	Register	DISP_VOP		
0	0 Disable		Disable		
1	1 Enable		Enable		

Set Control Register (Register Address – FFH)

Control Register								
Addr: FFH Write : Control(Register)=0x80H, Read : Control(Register)=0x00H								
D7	D6	D5	D4	D3	D2	D1	D0	
R/W	R	R	R	R	R	R	R	
W_EPROM	0	0	0	0	0	0	0	

W_EPROM							
Register	Bit Description						
0	Disable any registers data write into the EPROM						
1	Enable all register's data to write into the EPROM						

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Application Information

The device can be used for any applications that require positive and negative supplies, ranging from ±4V to ± 6V and current up to 150mA. The positive and negative output voltages are independently programmable by I2C interface and their sequencing is also independently programmable by external signals at ENP and ENN pins.

Boost Input Capacitor Selection

 $10\mu F$ or higher values of low ESR ceramic capacitors are recommended at input VIN pin. A minimum effective capacitance of $4\mu F$ is required at VIN pin. Considering capacitance de-rating with higher temperature and DC bias voltages, X7R, and 10V or 16V voltage rating are recommended.

Boost Inductor Selection

A 4.7µH inductor is recommended as shown in the table of Recommended Operating Conditions. In general, lower inductor DCR and larger inductor size support higher Boost conversion efficiency.

Boost Output Capacitor Selection

10μF or higher values of low ESR ceramic capacitors are recommended as shown in the table of Recommended Operating Conditions. A minimum effective capacitance of 4μF is required. Higher capacitor values and higher voltage ratings can be used to improve load transient response.

LDO Output Capacitor Selection

10μF or higher values of low ESR ceramic capacitors are recommended as shown in the table of Recommended Operating Conditions. A minimum effective capacitance of 4μF is required. Higher capacitor values and higher voltage ratings can be used to improve load transient response.

Charge Pump Output Capacitor Selection

10μF or higher values of low ESR ceramic capacitors are recommended as shown in the table of Recommended Operating Conditions. A minimum effective capacitance of 4μF is required. Higher capacitor values and higher voltage ratings can be used to improve load transient response.

Flying Capacitor Selection

A $2.2\mu\text{F}$ low ESR ceramic capacitor is recommended as shown in the table of Recommended Operating Conditions. Flying capacitor values directly impact the VON output voltage accuracy and load transient response. A minimum effective capacitance of $0.9\mu\text{F}$ is required at a DC bias of V_{ON} + 0.3V. For proper operation, the flying capacitor effective value must be lower than the Boost effective output capacitance.

Power-on and Power-off Sequence

If VOP and VON target voltages are set at higher than 5.2V, the power-on and power-off sequence is recommended as shown in Figure 11. If VOP and VON target voltages are set at lower than or equal to 5.2V, the power-on and power-off sequence is recommended as shown in Figure 12.

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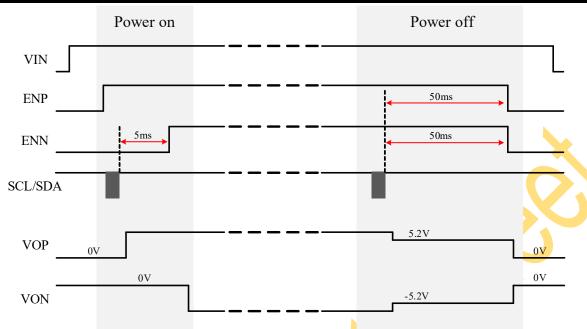


Figure 11. Power on/off sequence (VOP/VON >5.2V)

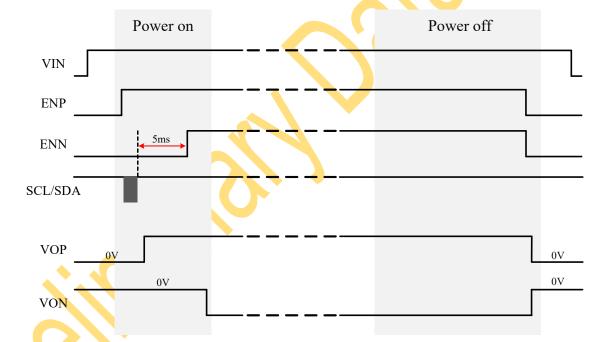


Figure 12. Power on/off sequence (VOP/VON≤5.2V)



PCB Layout Guideline

Appropriate PCB layout is important in the power supply design. Good PCB layout minimizes EMI and allows very good output voltage regulation. For the LP6820A, the following PCB layout guidelines are recommended.

- 1. Decouple VIN, REG, VOP and VON pins to PGND on the top layer and place decoupling capacitors as close to the pins as possible. Always avoid vias when possible because they have high inductance and resistance. If vias are necessary, always use more than one in parallel to decrease parasitics especially for power traces.
- 2. Connect AGND and PGND ground together with at least one uninterrupted ground plane, which include power ground and analog ground.
- 3. Place the flying capacitor as close as possible to the CFY1 and CFY2 pins and connect flying capacitors to the IC pins with short and wide traces.
- 4. Minimize trace length of SW node if possible to help reduce EMI emissions and noise that may couple into other portions of the converter.

An example of 2-layer PCB layout is shown in Figure 13.

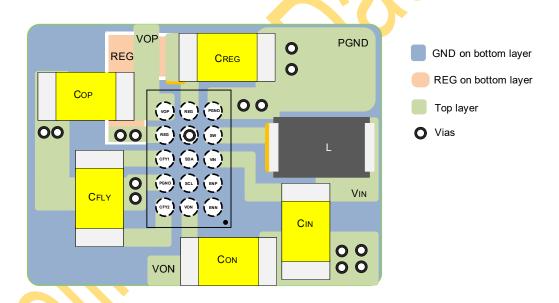


Figure 13. PCB Layout Example

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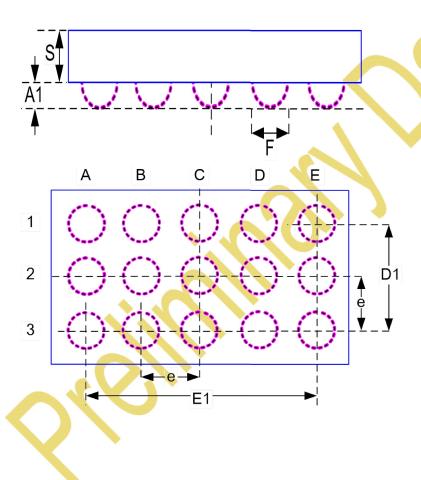


Package Information

WLCSP-15-ball Package (1.17×1.94) pitch 0.4 (Unit: mm)



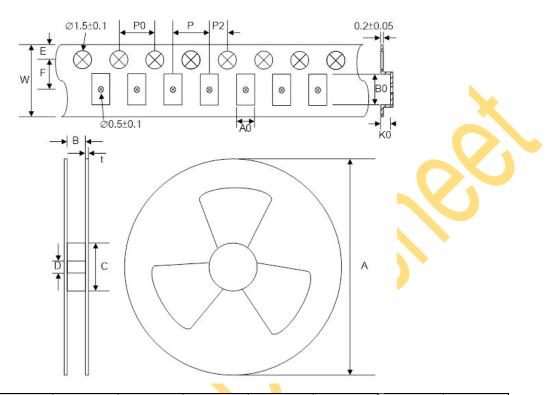
SYMBOLS	DIMENSION IN MILLIMETER				
UNIT	MIN	MAX			
D	1.145	1.185			
Е	1.915	1.955			
S	0.402	0.428			
D1	0.750	0.850			
E1	1.550	1.650			
A1	0.165	0.205			
F	0.210	0.250			
е	0.4				



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Carrier information



Device	Package Type		Pins	SPQ	A (mm)	B (mm)	C (mm)	D (mm)	t (mm)
	WLCSP		15	3000	ø180±1	9.5±0.5	Ø60±1	Ø13±0.2	1.1±0.25
LP6280A	W (mm)	E (mm)	F (mm)	P (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P2 (mm)
	8±0.3	1.75±0.1	3.5±0.05	4	1.82±0.05	2.74±0.05	0.75±0.05	4	2

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